L Number	Hits	Search Text	DB	Time stamp
1	691	(buried near (oxide or dielectric or	USPAT;	2004/07/25
		insulating) near (layer or film)) and	US-PGPUB;	15:25
		(substrate near5 surface) and ((epi or	EPO; JPO;	
		epitaxy or epitaxial) near (film or layer))	DERWENT;	
			IBM_TDB	
2	66	(buried near (oxide or dielectric or	USPAT;	2004/07/25
		insulating) near (layer or film)) same	US-PGPUB;	15:26
	•	(substrate near5 surface) same ((epi or	EPO; JPO;	10.20
		epitaxy or epitaxial) near (film or layer))	DERWENT;	
		cpitaxy of cpitaxial, fical (fillif of layer),	IBM_TDB	
3	6	((buried near (oxide or dielectric or	USPAT;	2004/07/25
•	·	insulating) near (layer or film)) same	1 *	15:29
			US-PGPUB;	15:25
		(substrate near5 surface) same ((epi or	EPO; JPO;	
		epitaxy or epitaxial) near (film or	DERWENT;	
	40	layer))).clm.	IBM_TDB	
4	16	((buried near (oxide or dielectric or	USPAT;	2004/07/25
		insulating) near (layer or film)) same	US-PGPUB;	15:30
		(substrate near5 surface) same ((epi or	EPO; JPO;	
		epitaxy or epitaxial) near (film or layer))	DERWENT;	
		same (semiconductor near (device or	IBM_TDB	
	:	element)))		
5	13	((buried adj (oxide or dielectric or	USPAT;	2004/07/25
		insulating) adj (layer or film)) same	US-PGPUB;	15:30
		(substrate near2 surface) same ((epi or	EPO; JPO;	
		epitaxy or epitaxial) near (film or layer))	DERWENT;	
		same (semiconductor near (device or element)))	IBM_TDB	
6	10	((buried adj (oxide or dielectric or	USPAT;	2004/07/25
		insulating) adj (layer or film)) same	US-PGPUB;	15:30
		(substrate near2 surface) same ((epi or	EPO; JPO;	10,00
		epitaxy or epitaxial) adj (film or layer))	DERWENT;	
		same (semiconductor near (body or device	IBM_TDB	
		or element)))	15105	
7	10	((buried adj (oxide or dielectric or	USPAT;	2004/07/25
•		insulating) adj (layer or film)) same		
		(substrate near2 surface) same ((epi or	US-PGPUB;	15:32
İ		, , , ,	EPO; JPO;	
		epitaxy or epitaxial) adj (film or layer))	DERWENT;	
		same (semiconductor adj (body or device or	IBM_TDB	
		element)))		
В	0	((buried adj (oxide or dielectric or	USPAT;	2004/07/25
		insulating) adj (layer or film)) same	US-PGPUB;	15:33
		(substrate near2 ((first or second or top or	EPO; JPO;	
		bottom) adj surface)) same ((epi or epitaxy	DERWENT;	
		or epitaxial) adj (film or layer)) same	IBM_TDB	
		(semiconductor adj (body or device or		
		element)))		
9	2	((buried adj (oxide or dielectric or	USPAT;	2004/07/25
		insulating) adj (layer or film)) same	US-PGPUB;	15:34
		(substrate near2 ((first or second or top or	EPO; JPO;	
		bottom) adj surface)) same ((epi or epitaxy	DERWENT;	
		or epitaxial) adj (film or layer)))	IBM_TDB	

10	207	(((oxide or dielectric or insulating) adj	USPAT;	2004/07/25
		(layer or film)) same (substrate near2 ((first	US-PGPUB;	15:35
		or second or top or bottom) adj surface))	EPO; JPO;	
		same ((epi or epitaxy or epitaxial) adj (film	DERWENT;	
		or layer)))	IBM_TDB	
11	29	(((oxide or dielectric or insulating) adj	USPAT;	2004/07/25
		(layer or film)) near10 (substrate near2	US-PGPUB;	15:39
		((first or second or top or bottom) adj	EPO; JPO;	
		surface)) near10 ((epi or epitaxy or	DERWENT;	
		epitaxial) adj (film or layer)))	IBM_TDB	
12	0	(((oxide or dielectric or insulating) adj	USPAT;	2004/07/25
		(layer or film)) near10 (substrate near2	US-PGPUB;	15:37
		((first or second or top or bottom) adj	EPO; JPO;	
		surface)) near10 ((epi or epitaxy or	DERWENT;	
		epitaxial) adj (film or layer))) and (buried	IBM_TDB	
		adj (oxide or insulating dielectric)).clm.		
13	0	(((oxide or dielectric or insulating) adj	USPAT;	2004/07/25
		(layer or film)) near10 (substrate near2	US-PGPUB;	15:37
		((first or second or top or bottom) adj	EPO; JPO;	
		surface)) near10 ((epi or epitaxy or	DERWENT;	
		epitaxial) adj (film or layer))).clm. and	IBM_TDB	
		(buried adj (oxide or insulating		
		dielectric)).clm.		
14	0	((((oxide or dielectric or insulating) adj	USPAT;	2004/07/25
		(layer or film)) near10 (substrate near2	US-PGPUB;	15:38
		((first or second or top or bottom) adj	EPO; JPO;	
		surface)) near10 ((epi or epitaxy or	DERWENT;	
		epitaxial) adj (film or layer)))) and (buried	IBM_TDB	
		near (oxide or dielectric or insulating)).clm.		
15	2	((((oxide or dielectric or insulating) adj	USPAT;	2004/07/25
		(layer or film)) near10 (substrate near2	US-PGPUB;	15:38
		((first or second or top or bottom) adj	EPO; JPO;	
	-	surface)) near10 ((epi or epitaxy or	DERWENT;	
		epitaxial) adj (film or layer)))) and (buried	IBM_TDB	
		near (oxide or dielectric or insulating))	_	